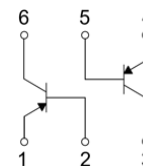


DUAL TRANSISTOR (PNP+PNP)

FEATURES

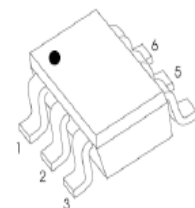
- Mounting possible with SOT-363 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area be cut in half.



Marking: T1

Absolute maximum ratings (Ta=25°C)

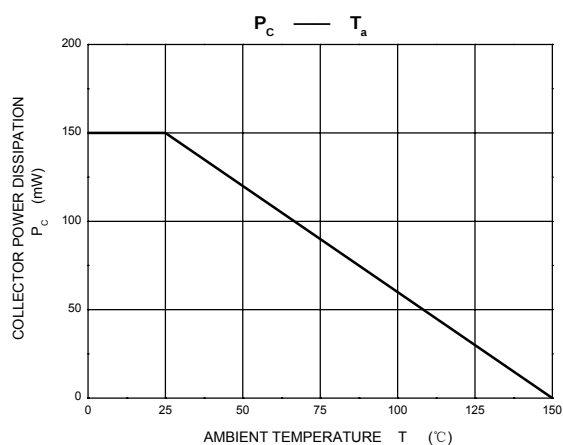
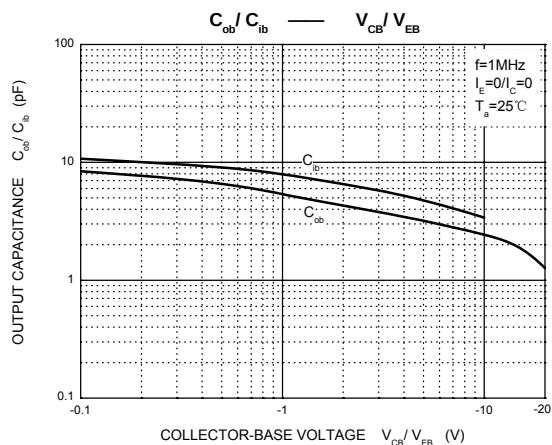
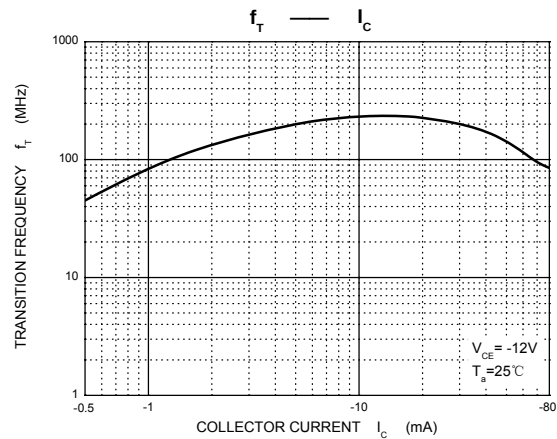
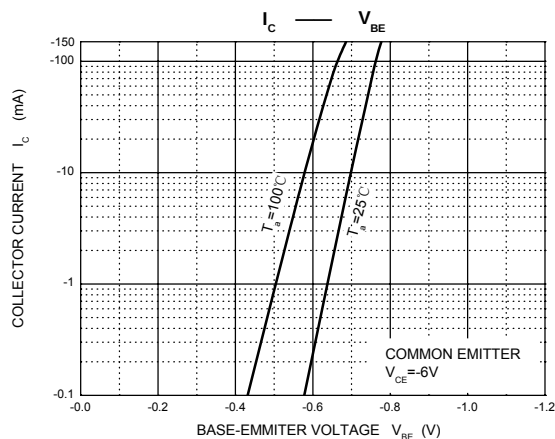
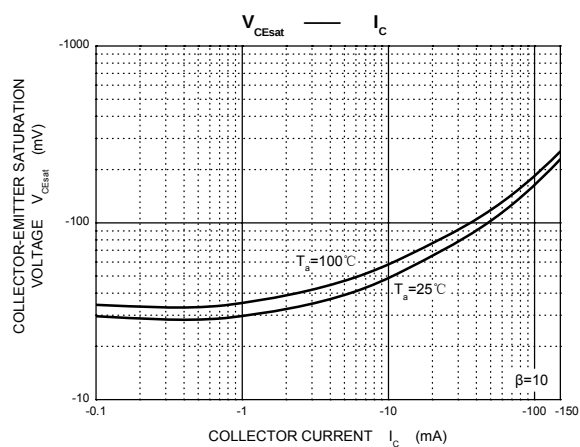
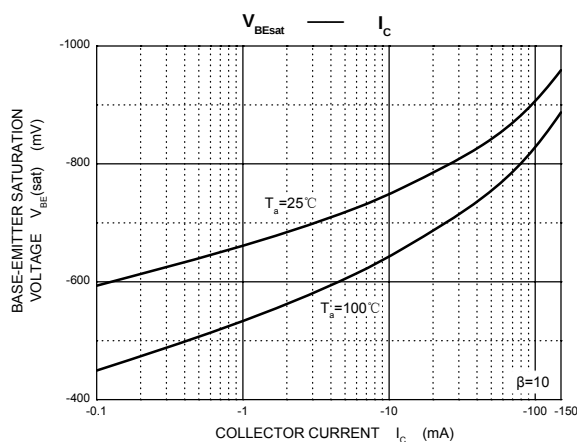
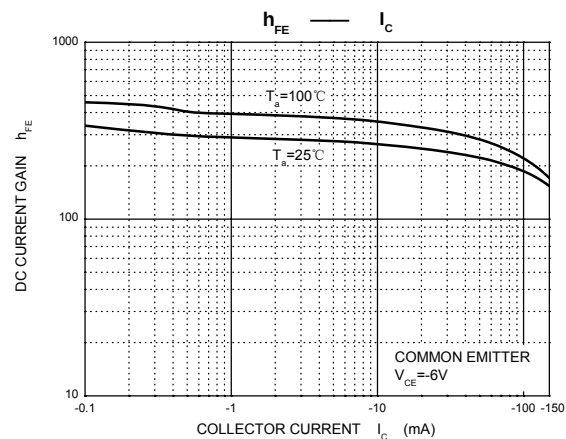
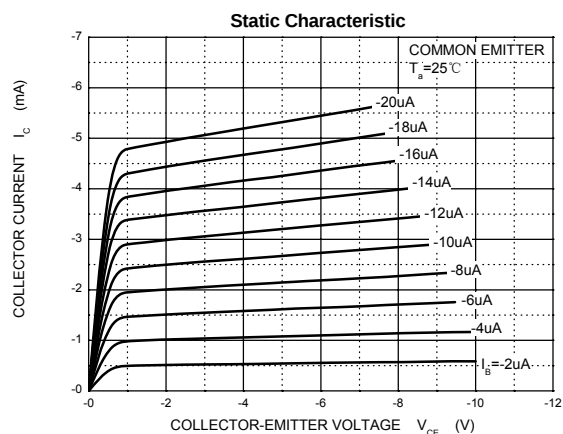
Symbol	Parameter	Limits	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Dissipation	150	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



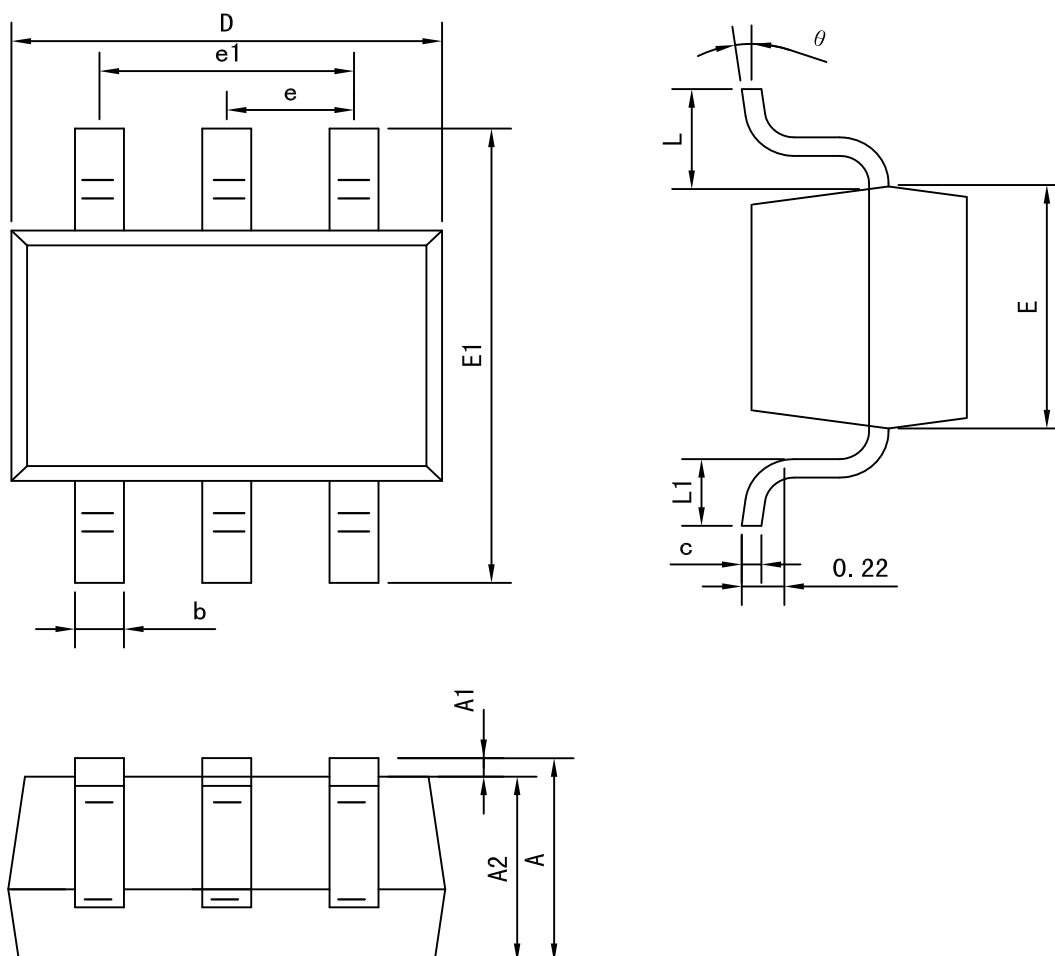
SOT-363

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-60			V
Collector-emitter breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-0.1	uA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	290		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.5	V
Transition frequency	f_T	$V_{CE} = -12V, I_E = 2mA, f = 100MHz$		140		MHz
Output capacitance	C_{ob}	$V_{CB} = -12V, I_E = 0, f = 1MHz$			5	pF



SOT-363 Package outline dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°